

WHAT IS CLAIMED IS:

1. A semiconductor switch driving circuit comprising:

a transformer;

a primary side area provided on the primary side of the transformer for controlling current on the primary side of the transformer according to a control signal for controlling a semiconductor switch; and

a secondary side area provided on the secondary side of the transformer for directly driving a switching device, voltage between the gate and the emitter of the switching device being continuously kept positive, voltage between the gate and the emitter being continuously kept negative and voltage between the gate and the emitter being alternately switched in positive and negative.

2. A semiconductor switch driving circuit according to Claim 1, wherein, in the primary side area, a control signal is input to transmit power for controlling plural switching devices to the secondary side area and back electromotive force caused when current flowing in the transformer is cut off is absorbed.

3. A semiconductor switch driving circuit according to Claim 1, the secondary side area receives the power supplied from the primary side area and transmits the power for controlling plural switching devices to the plural switching devices, and the plural

5 switching devices receive the power supplied to the secondary side
6 area of the semiconductor switch driving circuit and cause or
7 prevent current to flow for switching.

4. A semiconductor switch driving circuit according to Claim
1, wherein the source of P channel MOSFET is connected to a power
terminal, the drain of the P channel MOSFET is connected to the
anode of a diode, the cathode of the diode is connected to a terminal
at one end of a primary winding of a transformer and back
electromotive force between the terminal at one end of the primary
winding of the transformer and a terminal at the other end of the
primary winding of the transformer is inhibited when the P channel
MOSFET conducts.

5. A semiconductor switch driving circuit according to Claim
1, wherein in the primary side area, a control signal input terminal
(PL) is connected to the base of an NPN bipolar transistor (108)
via a resistor (105) and a capacitor (104) respectively connected
in parallel, the base and the emitter of the NPN bipolar transistor
(108) are connected via a resistor (106) and the emitter is connected
to a ground terminal (GND), the collector of the NPN bipolar
transistor (108) is connected to the gate of a P channel MOSFET
(110) via a resistor (107), the gate and the source of the P
channel MOSFET (110) are connected via a resistor (109) and the
source is connected to a power terminal (VDD), the drain of the P

12 channel MOSFET (110) is connected to the anode of a diode (111),
13 the cathode of the diode (111) is connected to the drain of a N
14 channel MOSFET (114) and a terminal (127a) of a primary winding
15 of a transformer (127), the gate and the source of the N channel
16 MOSFET (114) are connected via a resistor (113) and the source is
17 connected to a ground terminal (GND), a control signal input
18 terminal (N) is connected to the gate of the N channel MOSFET (114)
19 via a resistor (112), a control signal input terminal (NL) is
20 connected to the base of an NPN bipolar transistor (120) via a
21 resistor (117) and a capacitor (116) respectively connected in
22 parallel, the base and the emitter of the NPN bipolar transistor
23 (120) are connected via a resistor (118) and the emitter is connected
24 to a ground terminal (GND), the collector of the NPN bipolar
25 transistor (120) is connected to the gate of a P channel MOSFET
26 (122) via a resistor (119), the gate and the source of the P channel
27 MOSFET (122) are connected via a resistor (121) and the source is
28 connected to a power terminal (VDD), the drain of the P channel MOSFET
29 (122) is connected to the anode of a diode (123), the cathode of
30 the diode (123) is connected to the drain of a N channel MOSFET
31 (126) and a terminal (127d) of the primary winding of the transformer
32 (127), the gate and the source of the N channel MOSFET (126) are
33 connected via a resistor (125) and the source is connected to a
34 ground terminal (GND), a control signal input terminal (P) is
35 connected to the gate of the N channel MOSFET (126) via a resistor
36 (124), terminals (127b, 127c) of the primary winding of the

37 transformer 127 are connected to a center tap (135), the center
38 tap (135) is connected to a power terminal (VDD) and is connected
39 to a ground terminal (GND) via a capacitor (115).

Sub B2
1 6. A semiconductor switch driving circuit according to Claim
2 2, wherein the secondary side area is provided with plural switching
3 devices and plural gate driving sections for respectively directly
4 driving the switching device and the switching devices are
connected in series.

7. A semiconductor switch driving circuit according to Claim
6, wherein the switching device is an insulated gate bipolar
transistor (IGBT).

8. A semiconductor switch driving circuit according to Claim
1, wherein the secondary side area has a Zener diode for preventing
electromotive force generated on a secondary winding by back
electromotive force caused on a primary winding of the transformer.

9. A semiconductor switch driving circuit according to Claim
1, wherein, in the secondary side area, a terminal at one end of
a secondary winding of the transformer is connected to a first
Zener diode,

a second Zener diode is connected to a gate of a specific
switching device via a first resistor, wherein same kind of

7 polarities of the first and the second Zener diode are directly
8 connected in series with the polarities face to face,

9 a terminal at the other end of the secondary winding of the
10 transformer is connected to the emitter of the specific switching
11 device,

12 a second resistor and a capacitor are connected between the
13 second Zener diode and the emitter of the specific switching device,
14 and

15
16 wherein a structure comprising the secondary winding of the
17 transformer and the switching device connected via a gate driving
18 section is plurally provided.

Sub B3
10. An electrotherapy apparatus for supplying a high-voltage
electric pulse to a living body for electrotherapy comprising:

3 a semiconductor switch driving circuit containing:

4 a transformer;

5 a primary side area provided on the primary side of the
6 transformer for controlling current on the primary side of the
7 transformer according to a control signal for controlling a
8 semiconductor switch; and

9 a secondary side area provided on the secondary side of the
10 transformer for directly driving a switching device, voltage
11 between the gate and the emitter of the switching device being
12 continuously kept positive, voltage between the gate and the

